PBSS4350Z

NPN Transistors

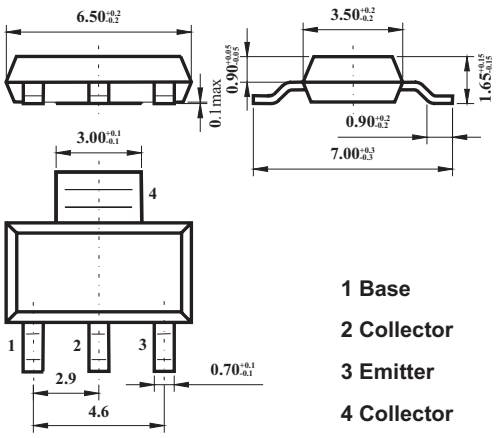
Features

- Excellent h_{FE} linearity and high h_{FE}

  Very low saturation voltage

SOT-223

Unit: mm



1 Base

2 Collector

3 Emitter

4 Collector

Absolute Maximum Ratings Ta = 25℃

Parameter	Symbol	Max	Unit
Collector to Base Voltage	V_{CBO}	60	V
Collector to Emitter Voltage	V_{CEO}	50	V
Emitter to Base Voltage	V_{EBO}	6	V
Collector Current to Continuous	I_C	3	A
Collector Dissipation	P_C	1.0	W
Junction Temperature	T_J	125	℃
Storage Temperature	T_{stg}	-55 to 150	℃

Electrical Characteristics Ta = 25℃

Parameter	Symbol	Testconditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	V_{CBO}	I_C=100uA ,I_E=0			60	V
Collector-emitter breakdown voltage	V_{CEO}	I_C= 10 mA , I_B=0			50	V
Emitter-base breakdown voltage	V_{EBO}	I_E= 100 uA ,I_C=0			6	V
Collector cut-off current	I_{CBO}	V_{CB}=40 V , I_E=0			1	uA
Collector cut-off current	I_{CEO}	V_{CE}=30 V , I_B=0			10	uA
Emitter cut-off current	I_{EBO}	V_{EB}=6V , I_C=0			1	uA
DC current gain	h_{FE}	V_{CE}= 2V, I_C= 1A	100			
		V_{CE}=2V, I_C= 100mA	50			
Collector-emitter saturation voltage	$V_{CE(sat)}$	I_C=2A, I_B= 0.2A			0.5	V
Base-emitter saturation voltage	$V_{BE(sat)}$	I_C=2A, I_B= 0.2A			1.5	V
Transition frequency	f_T	V_{CE}=5 V, I_C=0.1mA,f = 10MHz	50			MHz

■ Typical Characterisitics